

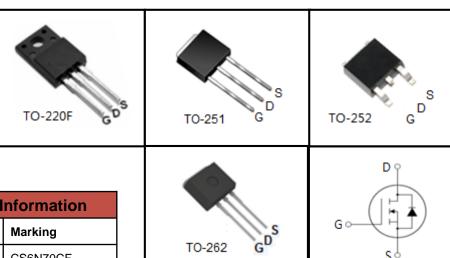
700V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information						
Device	Package	Marking				
CS6N70CF	TO-220F	CS6N70CF				
CS6N70CK	TO-262	CS6N70CK				
CS6N70CU	TO-251	CS6N70CU				
CS6N70CD	TO-252	CS6N70CD				

Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted							
Borometor	Symbol		l locit				
Parameter		TO-220F	TO-262	TO-251	TO-252	Unit	
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	700			V		
Continuous Drain Current	I _D	6			Α		
Pulsed Drain Current (note1)	I _{DM}	24			Α		
Gate-Source Voltage	V _{GSS}	±30			V		
Single Pulse Avalanche Energy (note2)	E _{AS}	139.4			mJ		
Avalanche Current (note1)	I _{AR}	5.28			Α		
Repetitive Avalanche Energy (note1)	E _{AR}	83.6			mJ		
Power Dissipation (T _C = 25°C)	P _D	63 97		W			
Operating Junction and Storage Temperature Range	T_J,T_stg	-55~+150				°C	

Thermal Resistance						
Baranatar	Symbol	Value				11
Parameter		TO-220F	TO-251	TO-252	TO-220	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	1.98		1.29		12/\\
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	60		K/W	



Specifications $T_J = 25^{\circ}C$, unless otherwise noted									
Parameter	Symbol	Test Conditions	Value			l lmit			
rarameter	Syllibol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	700			V			
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 700V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μΑ			
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$			±100	nA			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		4.0	V			
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_D = 3.0A$		1.3	1.6	Ω			
Dynamic									
Input Capacitance	C _{iss}	$V_{GS} = 0V$,		883.2		pF			
Output Capacitance	C _{oss}	$V_{DS} = 25V$,		87					
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		12					
Total Gate Charge	Q_g	$V_{DD} = 560V, I_{D} = 6.0A, V_{GS} = 10V$		29.5		nC			
Gate-Source Charge	Q_{gs}			4.2					
Gate-Drain Charge	Q_{gd}	55		15.2					
Turn-on Delay Time	t _{d(on)}			39.7		ns			
Turn-on Rise Time	t _r	$V_{DD} = 350V, I_{D} = 6.0A,$		20.2					
Turn-off Delay Time	t _{d(off)}	V_{DD} = 350V, I_D =6.0A, R_G = 25 Ω		134.5					
Turn-off Fall Time	t _f			34.9					
Drain-Source Body Diode Character	istics								
Continuous Body Diode Current	I _S	T 0500			6	А			
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			24				
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C$, $I_{SD} = 3.0A$, $V_{GS} = 0V$			1.4	V			
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V, I_{S} = 6.0A,$		633		ns			
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /μs		1.8		μC			

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}C$
- 3. Pulse Test: Pulse width ≤ 300µs, Duty Cycle ≤ 1%



Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted



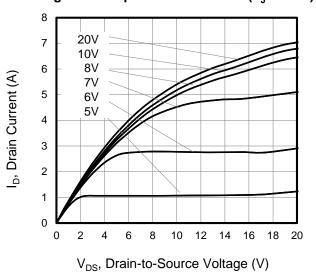


Figure 3. Drain Current vs. Temperature

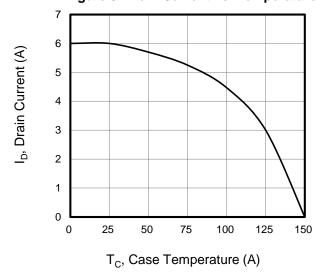


Figure 5. Transfer Characteristics

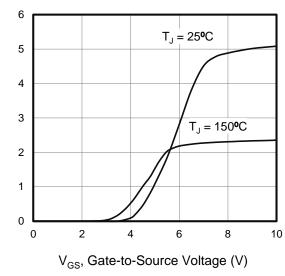


Figure 2. Body Diode Forward Voltage

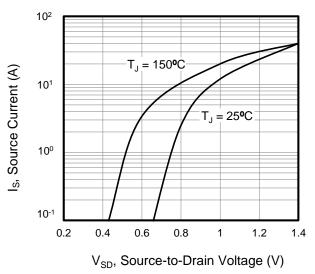


Figure 4. BV_{DSS} Variation vs. Temperature

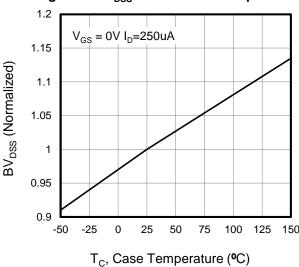
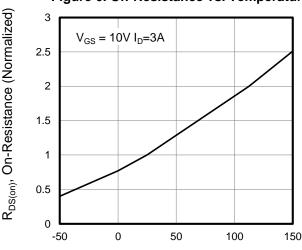


Figure 6. On-Resistance vs. Temperature



T_J, Junction Temperature (°C)

ID, Drain Current (A)



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

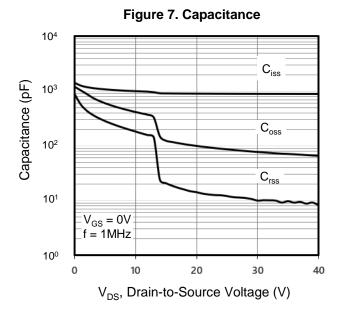


Figure 9. Transient Thermal Impedance TO-262,TO-251,TO-252

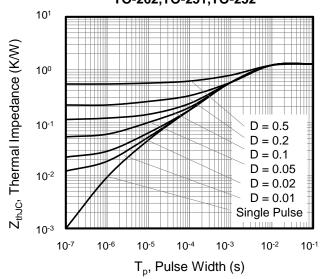


Figure 8. Gate Charge

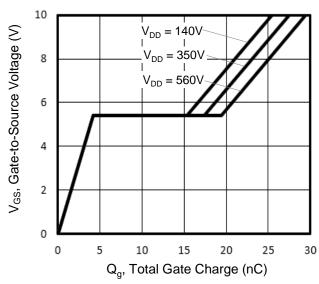


Figure 10. Transient Thermal Impedance

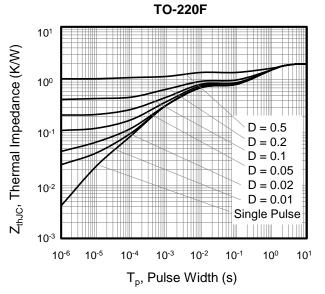




Figure A: Gate Charge Test Circuit and Waveform

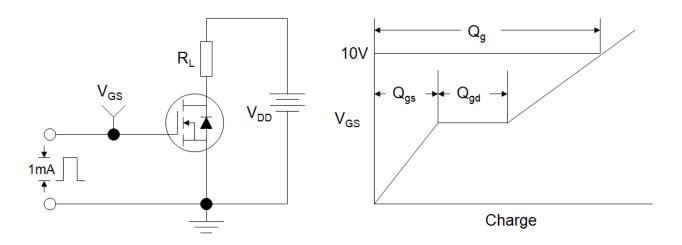


Figure B: Resistive Switching Test Circuit and Waveform

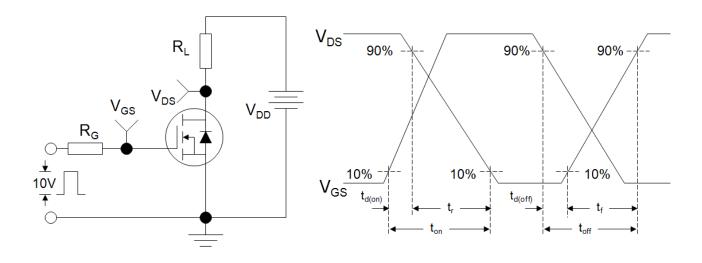
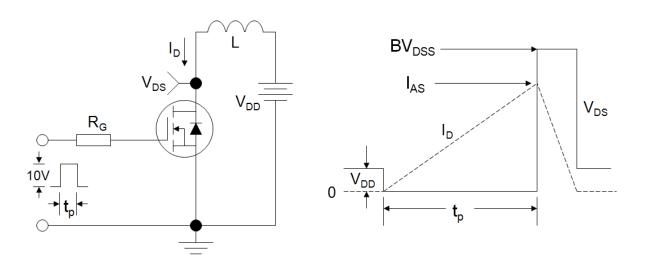
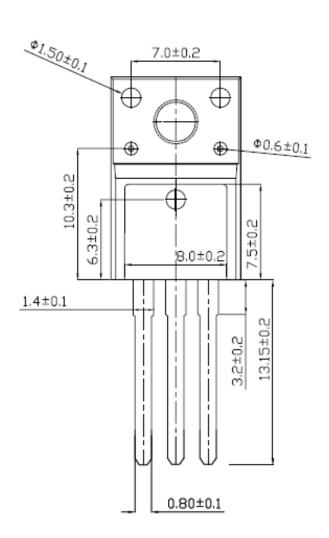


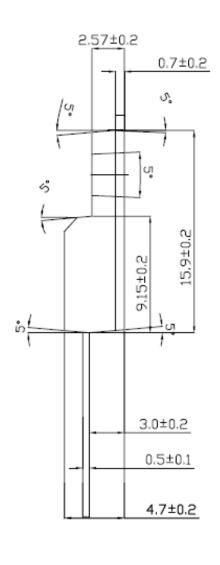
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





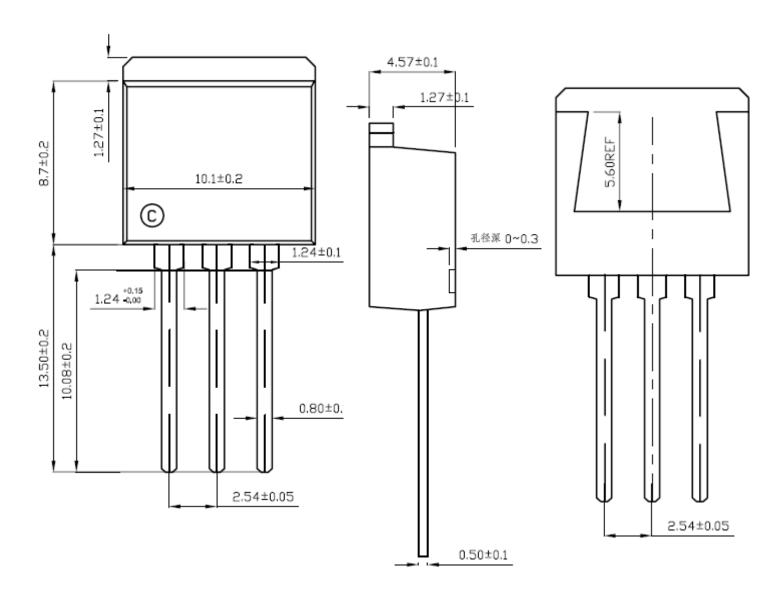
TO-220F





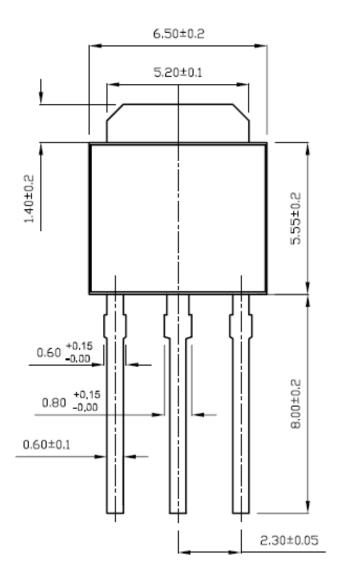


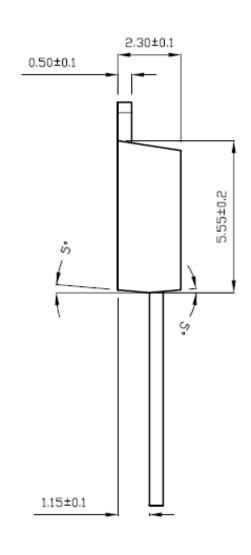
TO-262





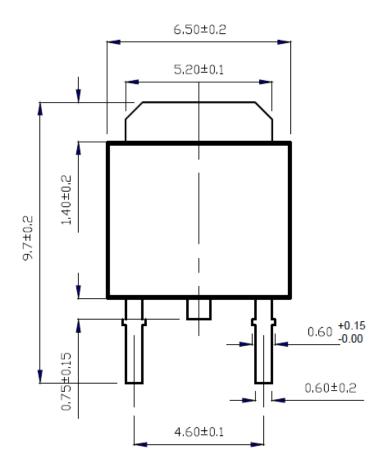
TO-251

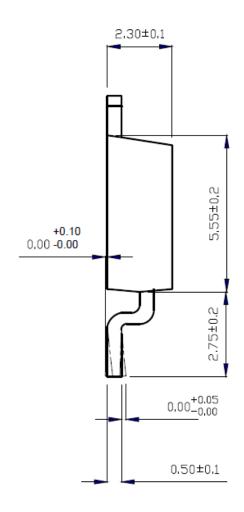






TO-252







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All product specifications and data are subject to change without notice.

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